# **AW318B Datasheet**

# Zhuhai Jieli Technology Co.,LTD

Version 1.2

Date 2025.01.17

Copyright © Zhuhai Jieli Technology Co.,LTD. All rights reserved.



# **Revision History**

Date	Revision	Description		
2024.04.12	V1.0	Initial Release		
2024.07.04	V1.1	Update IC Marking Information		
2025 04 47 1/4 2		Update Feature_Bluetooth		
2025.01.17	V1.2	Update BT Characteristics		





# **Table of Contents**

Re	vision History			1
Tal	ble of Contents			2
A۷	V318B Features			3
1	Block Diagram			4
2	Pin Definition			5
	2.1 Pin Assignment			5
	2.2 Pin Description			6
3				
	3.1 Absolute Maximum Ratings			7
	3.2 ESD Ratings			7
	3.3 PMU Characteristics			7
	3.4 IO Characteristics			8
	3.5 BT Characteristics			9
4	Package Information			. 10
		Y-17,7,0		
5	IC Marking Information		•••••	11
6	Solder-Reflow Condition			.12



## **AW318B Features**

#### **SYSTEM**

- > 32bit CPU 160MHz
- ➤ Support MATH/AES128
- I-cache
- Support EMU
- On-chip SRAM 32kbyte
- Support MPU
- Support UDMA
- ➢ Built-In Flash
- ➤ 24MHz crystal oscillator
- > Internal low jitter low power RC oscillator
- Internal PLL

#### **Bluetooth**

- BLE6.0 +2.4GHz-Proprietary (DN Q334307)
- Support AoA Transmitter
- Support long range BLE
- Maximum transmitting power 8dBm
- Receiver sensitivity
  - ◆ -92dBm @BLE-1Mbps
  - ❖ -89dBm @BLE-2Mbps

### **Peripherals**

- 1 x Full speed USB
- 4 x Multi-function 32bit timer
- ➤ 1 x IR RX/TX
- ➤ 1 x UART interface
- 1 x I<sup>2</sup>C Master/Slave interface
- 2 x SPI Master/Slave interface
- ➤ 1 x QDEC
- ➤ 2 x MCPWM
- ➤ 2 x LEDC
- 1 x 10bit ADC(2 Channel)
- 1 x GPIO Support function remapping

#### **PMU**

- Support temperature sensor
- ➤ VPWR range 2.7V to 5.5V
- ➢ IOVDD range 1.8V to 3.6V
- > Deep sleep mode (IOVDD @3.0V)
  - 170nA (External wakeup)
  - 1.37uA (32kHz RC OSC+wakeup)
  - 2.9uA (32kHz RC OSC+wakeup+16k retention SRAM)

#### **Packages**

➤ SOP8

#### **Temperature**

- Operating temperature
  - TC =  $-20^{\circ}$ C to  $+85^{\circ}$ C (standard range)
  - $TC = -40^{\circ}C$  to  $+105^{\circ}C$  (extended range)
- Storage temperature -65℃ to +150℃

#### **Applications**

- Mouse devices
- Non-audio remote controller
- Selfie stick
- Page turner
- Adaptive USB
- Bluetooth moudle
- Price tag and other diversified IOT product



# 1 Block Diagram

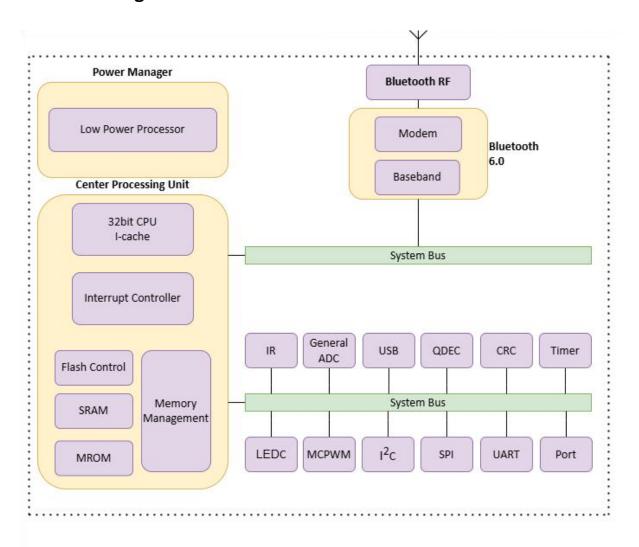


Figure 1-1 AW318B Block Diagram



### 2 Pin Definition

### 2.1 Pin Assignment

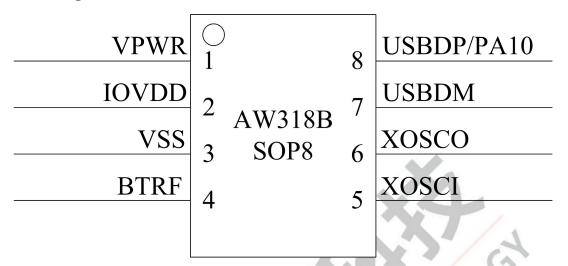


Figure 2-1 AW318B Pin Assignment

Copyright © 2024 Zhuhai Jieli Technology Co., LTD



### 2.2 Pin Description

Table 2-2-1 AW318B Pin Description

Pin No.	Name	Туре	IO Initial State	Description	
1	VPWR	Р		Battery Input	
2	IOVDD	Р		IO Power	
3	VSS	G		Ground	
4	BTRF	RF		Bluetooth RF Antenna	
5	XOSCI	ı		Crystal Oscillator Input	
6	xosco	0		Crystal Oscillator Output	
7	USBDM	1/0	15kΩ Pull-down	ADC13(ADC Input Channel 13)	
0	USBDP	1/0	15kΩ Pull-down	ADC14(ADC Input Channel 14)	
8	PA10	1/0	Z	ADC10(ADC Input Channel 10)	

#### Note

- 1.IO initial state abbreviations Z--High resistance, H--High level, L--Low level, X--May be changed during power on.
- 2.Timer, IR,MCPWM, QDEC, UART, LEDC, I<sup>2</sup>C, SPI1 functions can be remapped to any I/O.

**Table 2-2-2 Pin Types Description** 

Pin Type	Description	Pin Type	Description
Р	Power	1/0	Input or Output
G	Ground	1	Input
RF	RF antenna	0	Output



### **3** Electrical Characteristics

### 3.1 Absolute Maximum Ratings

**Table 3-1 Absolute Maximum Ratings** 

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-20	+85	$^{\circ}$
Tstg	Storage temperature	-65	+150	$^{\circ}$
VPWR	Const. Wells as	-0.3	6.0	V
IOVDD	Supply Voltage	-0.3	3.6	V
GPIO	Input voltage of GPIO (except PA7)	-0.3	3.6	V

#### Note

### 3.2 ESD Ratings

**Table 3-2 ESD Ratings** 

Parameter	Тур	Test pin	Reference standard
Human Body Mode	±8kV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±400V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±2kV	All pins	ANSI/ESDA/JEDEC JS-002-2022

### 3.3 PMU Characteristics

Table 3-3-1 PMU Characteristics under VPWR supply

The contract of the contract o						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VPWR	Power supply		2.7		5.5	٧
Operating mo	Operating mode					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Voltage output			3.0		V
טטעטו	Loading current	IOVDD=3.0V@VPWR = 3.7V			60	mA
Low Power m	ode					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Loading current	IOVDD=3.0V@VPWR = 3.7V			8	mA

Table 3-3-2 PMU Characteristics under IOVDD supply

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Power supply	-	1.8	-	3.6	V

<sup>1.</sup>Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device.



### 3.4 IO Characteristics

**Table 3-4 IO Characteristics** 

Innest Char	un aka ulakina		aracteristics			
	racteristics					
Symbol	Parameter	Conditions	10	Min	Max	Unit
$V_{IL}$	Low-Level Input Voltage	IOVDD = 3.0V	PA10	-0.3	1.4	V
$V_{IH}$	High-Level Input Voltage	IOVDD = 3.0V	USBDP	1.7	3.3	V
VIH	Trigit-Level input voitage	10 V D D = 3.0 V	USBDM	1.7	3.3	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Ch	aracteristics					
Symbol	Parameter	Conditions	10	Т	ур	Unit
I <sub>OL</sub>	Output Current	IOVDD = 3.0V Voutput = 0.3V	PA10	9(H 21(F	D=0) D=1) HD=2)	mA
, 62,		IOVDD = 3.0V Voutput = 0.3V	USBDP USBDM	54(HD=3) 8		mA
Іон	Output Current	IOVDD = 3.0V Voutput = 2.7V	PA10	3(HD=0) 9(HD=1) 21(HD=2) 54(HD=3)		mA
		IOVDD = 3.0V Voutput = 2.7V	USBDP USBDM	8		mA
Internal R	esistance Characteristics					
Symbol	Parameter	Conditions	10	Т	ур	Unit
		IOVDD = 3.0V	PA10	100k	PU=1) (PU=2)	Ω
$R_{pu}$	Pull-up Resistance	)		1M(	PU=3)	
		IOVDD = 3.0V	USBDP	1	.5k	Ω
		IOVDD = 3.0V	USBDM	18	30k	Ω
$R_{pd}$	Pull-down Resistance	IOVDD = 3.0V	PA10	100k	PD=1) (PD=2) PD=3)	Ω
		IOVDD = 3.0V	USBDP USBDM	15k		Ω

### Note

1.Internal pull-up/pull-down resistance accuracy ±20%.



### 3.5 BT Characteristics

### 3.5.1 Transmitter

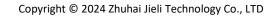
**Table 3-5-1 Transmitter characteristics** 

Parameter	Conditions	Min	Тур	Max	Unit
Maximum RF Transmit Power	BLE-1Mbps		7	8	dBm

### 3.5.2 Receiver

**Table 3-5-2 Receiver characteristics** 

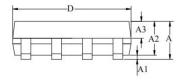
Parameter	Conditions	Min	Тур	Max	Unit
	BLE-1Mbps		-92		dBm
Canaitivity	BLE-2Mbps	//	-89		dBm
Sensitivity	BLE-S2	5	-95		dBm
	BLE-S8	-	-100	//	dBm

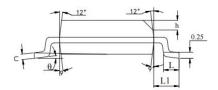


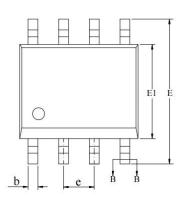


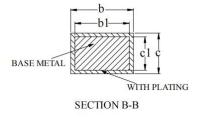
# 4 Package Information

### 4.1 SOP8









MILLIMETER SYMBOL NOM MAX MIN A 1.75 0.225 A1 0.10 1.30 1.50 A2 0.70 A3 0.60 0.39 0.47 b bl 0.38 0.44 0.41 0.20 0.24 0.19 0.20 0.21 c1 D 4.80 5.00 E 5.80 6.20 El 3.80 4.00 3.90 e 1.27BSC 0.50 h 0.25 0.50 0.80 L Ll 8° θ 0

Figure 4-1 AW318B Package



## 5 IC Marking Information

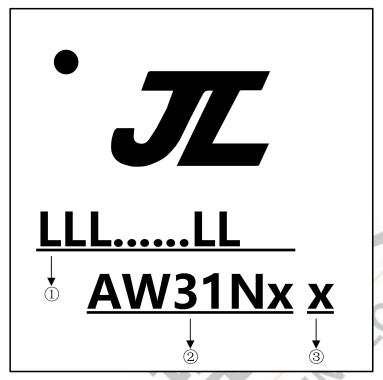


Figure 5-1 AW318B Package Outline

- 1 LLL.....LL LOT No. , It contains 7 to 18 alphanumerics
- 2 AW31Nx Chip Model
- (3) x Built-in flash size
  - 0 No Flash Memory
  - 2 2Mbit Flash
  - 4 4Mbit Flash



### 6 Solder-Reflow Condition

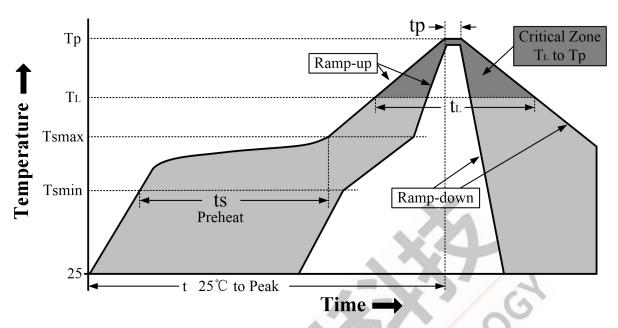


Figure 6-1 Classification Reflow Profile

**Table 6-1 Classification Profiles** 

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
	Temperature Min (T <sub>smin</sub> )	100℃	150℃
Preheat/Soak	Temperature Max (T <sub>smax</sub> )	150°C	200℃
	Time (ts) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds	60-180 seconds
Average ramp-	up rate (T <sub>smax</sub> to T <sub>p</sub> )	3℃/second max	3℃/second max
Liquidus temperature (T <sub>L</sub> )		183℃	217℃
Time (t <sub>L</sub> ) maint	ained above T∟	60-150 seconds	60-150 seconds
Peak package b	ood <mark>y temperature (T<sub>p</sub>)</mark>	See Table 6-2	See Table 6-3
Time within 5°0	C of actual	10-30 seconds	20-40 seconds
Peak Temperature (tp) <sup>2</sup>		10-50 Seconds	20-40 seconds
Ramp-down rate (Tp to TL)		6℃/second max	6℃/second max
Time 25℃ to p	eak temperature	6 minutes max	8 minutes max

#### Note

- 1.All temperatures refer to topside of the package, measured on the package body surface
- 2.Time within 5  $^{\circ}$ C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" and "user" maximum.

**Table 6-2 SnPb Classification Temperature** 

Package	Volume mm <sup>3</sup>	Volume mm³ ≥ 350	
Thickness	< 350		
<2.5 mm	240 +0/-5℃	225 +0/-5°C	
≥2.5 mm	225 +0/-5℃	225 +0/-5°C	



**Table 6-3 Pb-free - Classification Temperature** 

	·		
Package	Volume mm³	Volume mm³	Volume mm³
Thickness	< 350	350 - 2000	> 2000
< 1.6mm	260℃	260℃	<b>260</b> ℃
1.6 mm - 2.5mm	260℃	250℃	245℃
> 2.5mm	250℃	245℃	245℃

#### Note

1.\*Tolerance The device manufacturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0  $^{\circ}$ C.For example 260  $^{\circ}$ C+0  $^{\circ}$ C)at the rated MSL level.

